

# FINAL PRODUCT/PROCESS CHANGE NOTIFICATION#16441B

Generic Copy

### Issue Date: 12-Sep-2012

**<u>TITLE</u>**: NCS2200A, NCS2220A, NCP69x, NCP600 and NCV8560 Device Families Qualification at Gresham Wafer Fab

#### PROPOSED FIRST SHIP DATE: 12-Dec-2012

AFFECTED CHANGE CATEGORY(S): Wafer Fab Location

### FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office <u>Shannon.Riggs@onsemi.com</u> or <u>Alan.Garlington@onsemi.com</u>

**SAMPLES:** Contact your local ON Semiconductor Sales Office or <u>Tim.Gurnett@onsemi.com</u> or <u>Bett.lofts@onsemi.com</u>

#### ADDITIONAL RELIABILITY DATA: Available

Contact your local ON Semiconductor Sales Office or Ken.Fergus@onsemi.com

### NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.

### **DESCRIPTION AND PURPOSE:**

ON Semiconductor is pleased to announce the Wafer Fab qualification for the Device families which are listed below. These device families are currently qualified at ON Semiconductor's Aizu wafer fab facility located in Aizu, Japan and are now qualified at ON Semiconductor's Gresham wafer fabrication facility located in Gresham, Oregon. Per the earlier announcement by ON Semiconductor, the Aizu Wafer fab is scheduled to be closed in the future which necessitates this transfer. Upon expiration (or approval) of this Final PCN, devices listed in this notice may be supplied by either wafer fab.

The Gresham wafer fab is compliant to ISO9001:2008, ISO/TS16949:2009, and ISO14001:2004. All devices affected by this PCN are currently run on the Aizu ACMOS2 process. The same ACMOS2 process has been transferred to and successfully qualified at the Gresham wafer fab. No device design changes have been made. Device performance is the same for Aizu and Gresham-sourced devices.

All of these device families will continue to be assembled and tested in existing, qualified locations. No changes to packaging will occur as a result of this fab qualification.



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## **RELIABILITY DATA SUMMARY:**

## Devices used for New Wafer Fab Qualification: 3 Device families

Device	NCP303LSN30T1G	Wafer Fab Site	Gresham	Oregon, USA
Package	TSOP-5	Assembly Site	SBN	Seremban, Malaysia
MSL Level	MSL 1 @260℃	Final Test Site	SBN	Seremban, Malaysia
Technology	ACMOS 2			
Final Lead Finish	Pb free	Package Code	0670	
Device	NCV8560MNADJR2G	Wafer Fab Site	Gresham	Oregon, USA
Package	DFN 6 3*3	Assembly Site	SBN	Seremban, Malaysia
MSL Level	MSL 1 @260℃	Final Test Site	SBN	Seremban, Malaysia
Technology	ACMOS 2			
Final Lead Finish	Pb free	Package Code	0448	
Device	NCP5208DR2G	Wafer Fab Site	Gresham	Oregon, USA
Package	SOIC-8 NB	Assembly Site	OSPI	Carmona,
				Philippines
MSL Level	MSL 1 @260℃	Final Test Site	OSPI	Carmona, Philippines
Technology	ACMOS 2			
Final Lead Finish	Matte Sn	Package Code	0081	

#### **Reliability Test Results:**

The Gresham-sourced Device families were all qualified by similarity based on the successful platform qual of the ACMOS2 technology and qualification device data as follows:



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### Device NCP303LSN30T1G AEC Grading level 1 – Operating T° grading: -40°C to +125°C

Test	Name	Test Conditions	End Point Req's	Read Point (rej/ ss)		(rej/ ss)
				Qual Lot		Control lot
HTOL	High Temp Op Life	Ta = 125℃ Tj = 125℃ For <b>504 hrs</b>	c = 0, Cold, Room, Hot	<b>504Hrs</b> 1008 Hrs	0/80 (a) 0/80	0/80 0/80
ELFR	Early failure rate	Ta = 125℃ For <b>48 hrs</b>	c = 0, Cold, Room, Hot	48hrs		0/800
PC-TC	Temp Cycle (units mounted on daughter card)	MSL1 preconditioning -65/+150 C, air to air For <b>500 cyc</b>	c = 0, Room, hot	<b>500 cyc</b> 1000 cyc	0/84 0/84	0/84 0/84
PC-UHAST	Unbiased HAST TEST	MSL1 preconditioning TA= +130C, RH = 85%, PSIG= 18.8, NO bias	c = 0, Room	96 hrs	0/84	0/84
PC-HAST	HAST TEST	MSL1 preconditioning TA= +130C, RH = 85%, PSIG= 18.8, bias	c = 0, Room, hot	<b>96 hrs</b> 0/84		0/84
SAT	SAT	MSL1@260℃ (delamination on di	e)		0/5	0/5
HTOL	High Temp Op Life	Ta = 125 <i>°</i> C Tj = 125 <i>°</i> C For <b>504 hrs</b>	c = 0, Room, Hot	<b>504Hrs</b> 1008 Hrs		0/80 0/80
PC-TC	Temp Cycle (units mounted on daughter card)	MSL1 preconditioning -65/+150 C, air to air For <b>500 cyc</b>	c = 0, Room, hot	500 сус		0/84
HTSL	High Temperature Storage Life Test	Ta=150 <i>°</i> C	c = 0, Room	504Hrs <b>1008 Hrs</b>		0/80 0/80

					<u>Qual Lot</u>	<u>Control</u>
LU	Latch-up	Class II / 85℃	C=0, Room, hot	LU+>200 mA LU - >200mA	Pass Pass	Pass Pass
ESD	Electro-static Discharge	Human Body Model (HBM), Machine (MM) Charge device Model (CDM)	c = 0, Room, Hot	Results	HBM : +/- 3.5kV MM : +/- 200V CDM : 600V	HBM : +/- 4kV MM : +/- 300V CDM : 600V



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Device NCV8560MNADJR2G AEC Grading level 1 – Operating T° grading: -40 °C to +125 °C							
#	Test	Name	Test Conditions	Read Point	(rej∕ ss) <u>Qual Lot</u>	(rej/ ss) Control <u>lot</u>	
ELFR	Early Life Failure Rate	TA = 125℃	c = 0, Room, hot	48 hrs		0/810	
HTOL	High Temp Operating Live Test	TA = 104°C ; Tj=125℃	c = 0, Room, hot	504hrs. 1008 hrs	0/84 0/80	0/80 0/80	
PC	MSL1 Preconditioning	3 IR @ 245 deg C	c = 0, Room		0/262	0/262	
PC-UHST	Precon Unbias HAST	TA= +130C, RH = 85%, PSIG= 18.8	c = 0, Room	96hrs	0/84	0/84	
PC-TC	Precon Temp Cycle	-65/+150 ℃, Air to Air	c = 0, Room, hot	<b>500cyc</b> 1000 cyc	0/84 0/84	0/84 0/84	
		<b>TA</b> (220					
PC-HAST	Precond HAST	I A= +130C, RH = 85%, PSIG= 18.8, bias	c = 0, Room, hot	96 hrs	0/84	0/84	
SAT	Scanning Acoustic Tomography	Compare for Delamination before and after PC	Compare to existing data	Results	0/5	0/5	
ESD	Electro-static Discharge	Human Body Model (HBM) Machin Model (MM)	c = 0, Room, hot	Results	4kV 200V		
LU	Latch-up	Class II	c = 0, Room, hot	Results	LU+>1 LU->1	00mA 00mA	



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#	Test	Name	Test Conditions	End Point Req's	Test Results	Lot A (rej/ ss)	Lot B (rej/ ss)	Lot C (rej/ ss)	Control (rej/ ss)
2	HTOL	High Temp Op Life	TA = 125℃ for 1008hrs	c = 0, Room	504 hrs 1008 hrs	0/80 0/80	0/80 0/80	0/80 0/80	0/80 0/80
3	ELFR	Early Life Failure Rate	TA = 125℃	c = 0, Room	48hrs	0/800			
4	SAT	Scanning Acoustic Tomography	Compare for Delaminatio n before and after PC MSL 1 @260 ℃	Per 12MSB 17722 C	Results	0/5	0/5	0/5	0/5
5	PC	Moisture Preconditioning	MSL 1 @ 260 <i>°</i> C	c = 0, Room	After PC	0/240	0/240	0/240	0/240
6	UHAS T-PC	Precond. Autoclave	TA= +130 °C, RH = 85%, PSIG= 18.8, No bias	c = 0, Room	<b>96 hrs</b> 144 hrs	0/80 0/80	0/80 0/80	0/80 0/80	0/80 0/80
7	TC-PC	Precond. Temp Cycle	-65/+150 ℃ air to air	c = 0, Room	<b>500</b> <b>cycs</b> 1000 cyc	0/80 0/80	0/80 0/80	0/80 0/80	0/80 0/80
8	HAST- PC	Precond. HAST	TA= +130°C, RH = 85%, PSIG= 18.8, bias	c = 0, Room	<b>96 hrs</b> 144 hrs	0/80 0/80	0/80 0/80	0/80 0/80	0/80 0/80

ESD

Device =

NCP5208DR2G

Human Body ModelAll Families Pass 2000VMachine Model PassAll Families Pass 200V



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### ELECTRICAL CHARACTERISTIC SUMMARY:

Electrical characterization has been completed with no changes to the AC/DC specifications. ON Semiconductor recommends samples are obtained for application specific review. Data is available upon request.

Analysis of ESD capability resulted in some device specifications changing. The ESD specification for Machine Model (MM) will change from 400v to 200v for the following devices. The individual device data sheets will be changed accordingly.

NCP600 family NCP603 family NCP605 family NCP606 family NCP690 family NCP691 family NCP692 family NCV8560 family NCV8603 family NCV8605 family NCV8606 family

### CHANGED PART IDENTIFICATION:

Devices with date codes of 2012 work week 50 or later may be sourced from either wafer Gresham or Aizu fab.



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#### List of affected General Parts:

NCS2200AMUT1G NCS2220AMUT1G NCP600MN130R2G NCP600SN130T1G NCP600SN150T1G NCP600SN180T1G NCP600SN250T1G NCP600SN280T1G NCP600SN300T1G NCP600SN330T1G NCP600SN350T1G NCP600SN500T1G NCP600SNADJT1G NCP603SN130T1G NCP603SN150T1G NCP603SN180T1G NCP603SN250T1G NCP603SN280T1G NCP603SN300T1G NCP603SN330T1G NCP603SN350T1G NCP603SN500T1G NCP603SNADJT1G NCP605MN15T2G NCP605MN18T2G NCP605MN25T2G NCP605MN28T2G NCP605MN30T2G NCP605MN33T2G NCP605MN50T2G NCP605MNADJT2G NCP606MN15T2G NCP606MN18T2G NCP606MN25T2G NCP606MN28T2G NCP606MN30T2G NCP606MN33T2G NCP606MN50T2G NCP606MNADJT2G NCP690MN15T2G NCP690MN18T2G NCP690MN25T2G NCP690MN33T2G NCP690MN50T2G NCP690MNADJT2G NCP691MN15T2G NCP691MN18T2G

NCP691MN25T2G NCP691MN33T2G NCP691MN50T2G NCP691MNADJT2G NCP692MN15T2G NCP692MN18T2G NCP692MN25T2G NCP692MN33T2G NCP692MN50T2G NCP692MNADJT2G NCV8560MN150R2G NCV8560MN180R2G NCV8560MN250R2G NCV8560MN280R2G NCV8560MN300R2G NCV8560MN330R2G NCV8560MN350R2G NCV8560MN500R2G NCV8560MNADJR2G NCV8560SN130T1G NCV8560SN150T1G NCV8560SN180T1G NCV8560SN250T1G NCV8560SN280T1G NCV8560SN300T1G NCV8560SN330T1G NCV8560SN350T1G NCV8560SN500T1G NCV8560SNADJT1G NCV8603SN33T1G NCV8605MN15T2G NCV8605MN18T2G NCV8605MN25T2G NCV8605MN28T2G NCV8605MN30T2G NCV8605MN33T2G NCV8605MN50T2G NCV8605MNADJT2G NCV8606MN15T2G NCV8606MN18T2G NCV8606MN25T2G NCV8606MN28T2G NCV8606MN30T2G NCV8606MN33T2G NCV8606MN50T2G NCV8606MNADJT2G

### List of affected Customer Specific Parts:

SCY99155MUT1G